

Supporting Information for

## Printed In-Ga-Zn-O drop-based thin-film transistors sintered using intensely pulsed white light

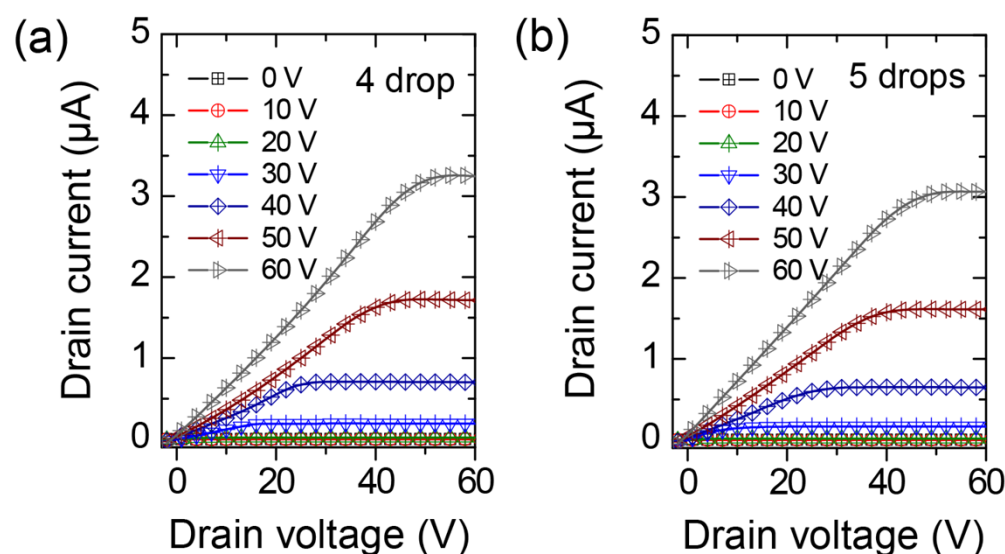
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**Figure S1.** Output characteristics of IGZO TFTs with 4 drops (a) and 5 drops (b).